

GALLIUM NITRIDE SERIES COMPOUND SEMICONDUCTOR LASER ELEMENT

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Abstract

PURPOSE: To provide the gallium nitride based compound semiconductor laser element of surface emission type in which a laser resonator is formed in the vertical direction to a substrate by forming an appropriate reflecting mirror in a gallium nitride based compound semiconductor.
CONSTITUTION: In a laser element of double hetero structure comprising a gallium nitride based compound semiconductor, a first reflecting mirror 12 and a second reflecting mirror 3 are formed in the parallel direction to a substrate 1 by interposing an active layer 4 therebetween and a laser resonator is formed in the vertical direction to the substrate and the first reflecting mirror 12 is a translucent electrode in which an ohmic contact is obtained.

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